

MOS FIELD EFFECT TRANSISTOR
2SJ449

SWITCHING
 P-CHANNEL POWER MOS FET
 INDUSTRIAL USE

DESCRIPTION

The 2SJ449 is P-Channel MOS Field Effect Transistor designed for high voltage switching applications.

FEATURES

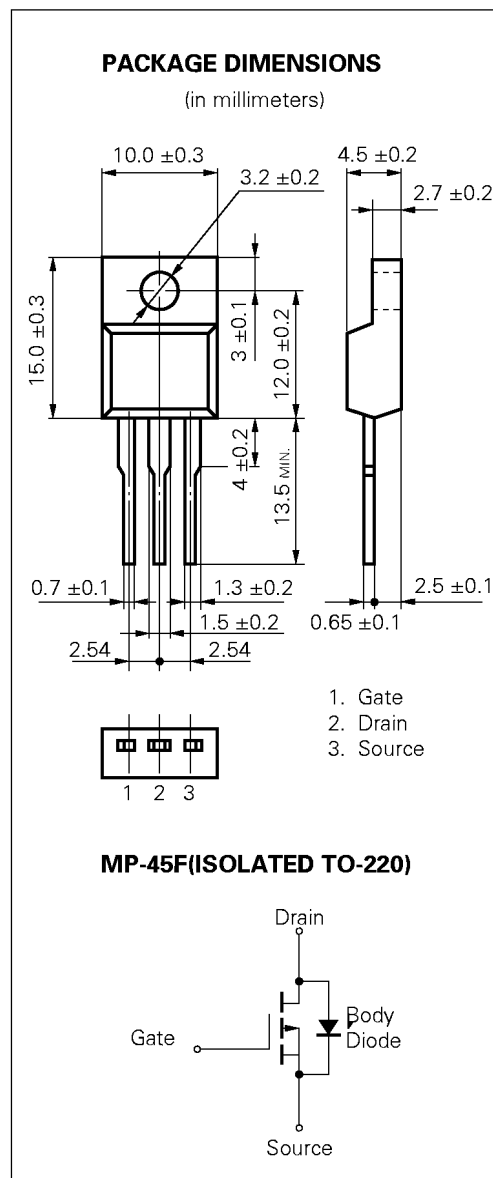
- Low On-Resistance
 $R_{DS(on)} = 0.8 \Omega \text{ MAX. (@ } V_{GS} = -10 \text{ V, } I_D = -3.0 \text{ A)}$
- Low C_{iss} $C_{iss} = 1040 \text{ pF TYP.}$
- High Avalanche Capability Ratings
- Isolated TO-220 Package

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 \text{ }^\circ\text{C}$)

Drain to Source Voltage	V_{DSS}	-250	V
Gate to Source Voltage	V_{GSS}	∓ 30	V
Drain Current (DC)	$I_{D(DC)}$	∓ 6.0	A
Drain Current (pulse)*	$I_{D(pulse)}$	∓ 24	A
Total Power Dissipation ($T_c = 25 \text{ }^\circ\text{C}$)	P_{T1}	35	W
Total Power Dissipation ($T_A = 25 \text{ }^\circ\text{C}$)	P_{T2}	2.0	W
Channel Temperature	T_{ch}	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$
Single Avalanche Current**	I_{AS}	-6.0	A
Single Avalanche Energy**	E_{AS}	180	mJ

* $PW \leq 10 \mu\text{s}$, Duty Cycle $\leq 1 \%$

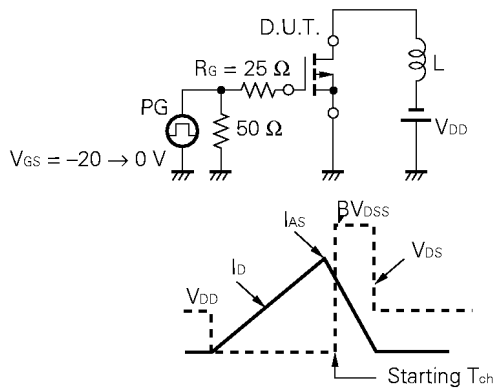
** Starting $T_{ch} = 25 \text{ }^\circ\text{C}$, $R_G = 25 \Omega$, $V_{GS} = -20 \text{ V} \rightarrow 0$



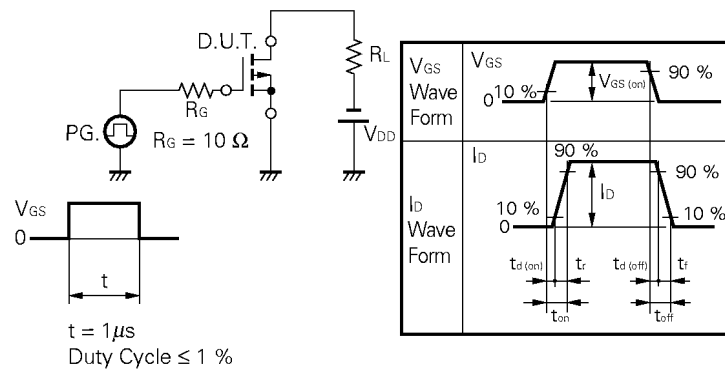
ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Drain to Source On-Resistance	R _{DS(on)}		0.55	0.8	Ω	V _{GS} = -10 V, I _D = -3.0 A
Gate to Source Cutoff Voltage	V _{GS(off)}	-4.0	-4.8	-5.5	V	V _{DS} = -10 V, I _D = -1 mA
Forward Transfer Admittance	y _{fs}	2.0	3.5		S	V _{DS} = -10 V, I _D = -3.0 A
Drain Leakage Current	I _{DSS}			-100	μA	V _{DS} = -250 V, V _{GS} = 0
Gate to Source Leakage Current	I _{GSS}			±100	nA	V _{GS} = ±30 V, V _{DS} = 0
Input Capacitance	C _{iss}		1040		pF	V _{DS} = -10 V
Output Capacitance	C _{oss}		360		pF	V _{GS} = 0
Reverse Transfer Capacitance	C _{rss}		70		pF	f = 1 MHz
Turn-On Delay Time	t _{d(on)}		24		ns	I _D = -3.0 A
Rise Time	t _r		16		ns	V _{GS(on)} = -10 V
Turn-Off Delay Time	t _{d(off)}		47		ns	V _{DD} = -125 V
Fall Time	t _f		14		ns	R _G = 10 Ω, R _L = 42 Ω
Total Gate Charge	Q _G		23.1		nC	I _D = -6.0 A
Gate to Source Charge	Q _{GS}		7.1		nC	V _{DD} = -200 V
Gate to Drain Charge	Q _{GD}		12.9		nC	V _{GS} = -10 V
Body Diode Forward Voltage	V _{F(S-D)}		0.92		V	I _F = -6.0 A, V _{GS} = 0
Reverse Recovery Time	t _{rr}		155		ns	I _F = -6.0 A, V _{GS} = 0
Reverse Recovery Charge	Q _{rr}		930		nC	di/dt = 50 A/μs

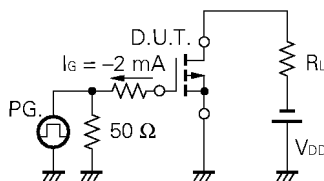
Test Circuit 1 Avalanche Capability



Test Circuit 2 Switching Time

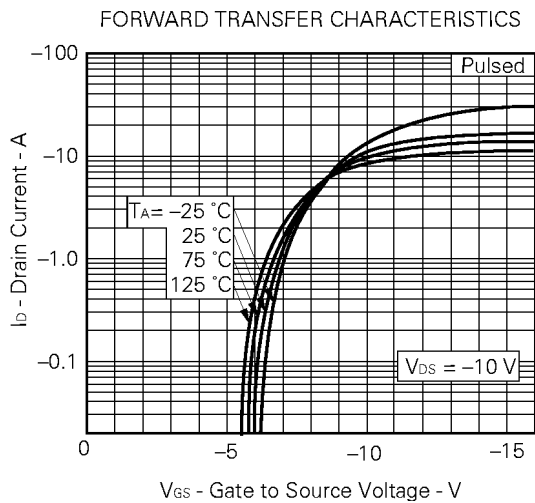
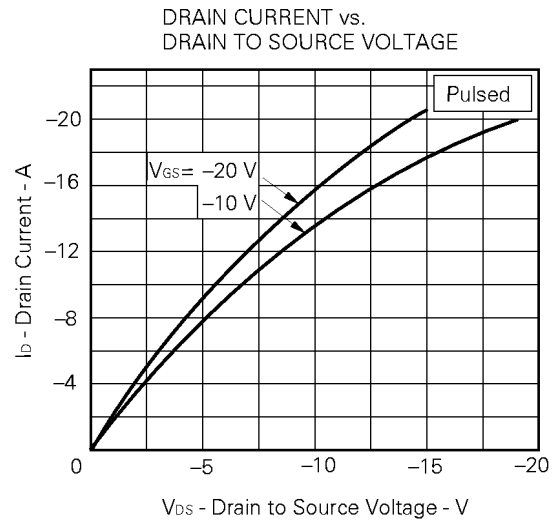
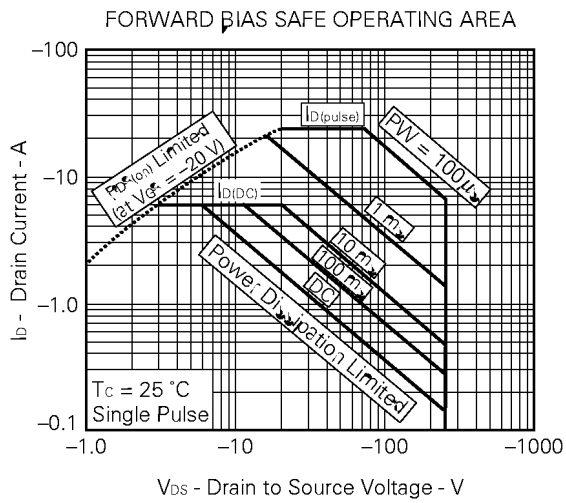
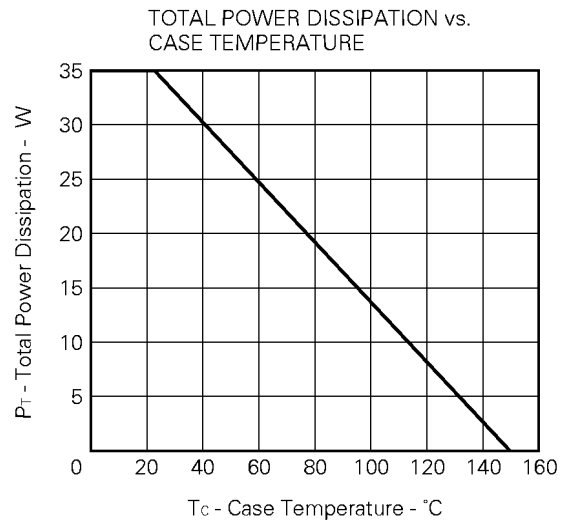
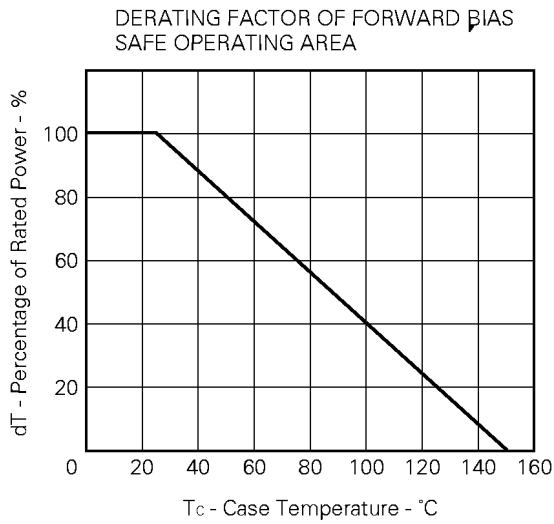


Test Circuit 3 Gate Charge

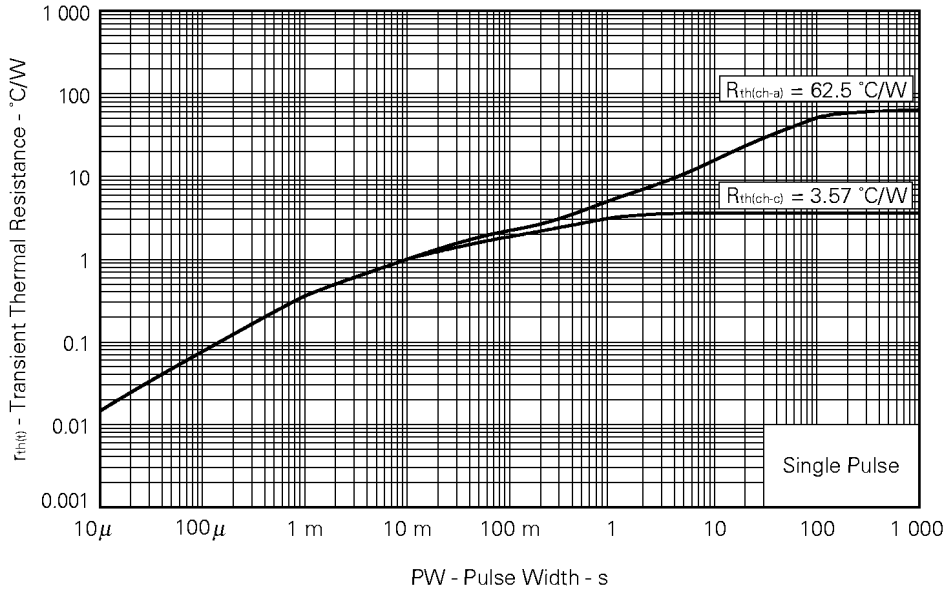


The application circuits and their parameters are for references only and are not intended for use in actual design-in's.

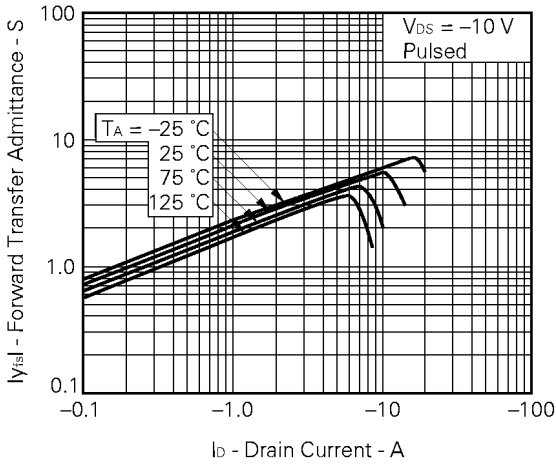
TYPICAL CHARACTERISTICS (T_A = 25 °C)



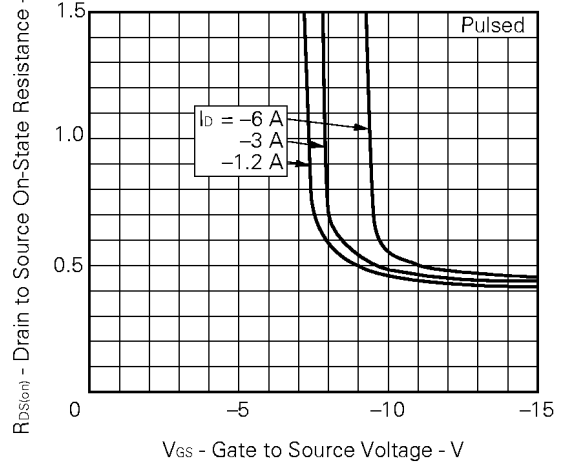
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



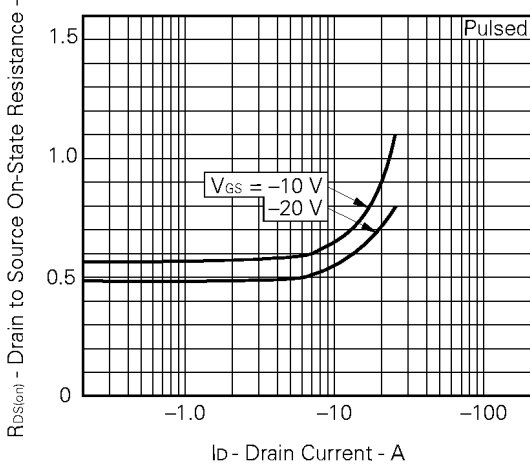
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



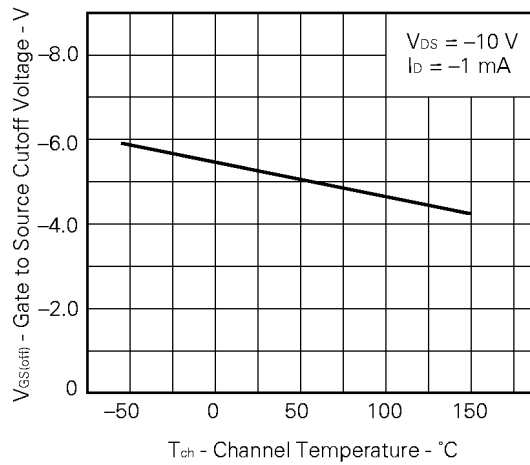
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



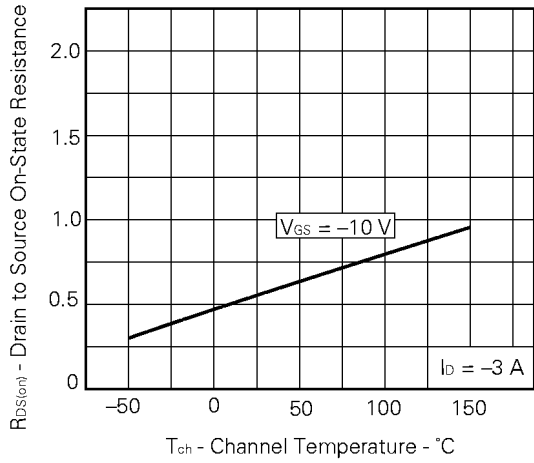
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



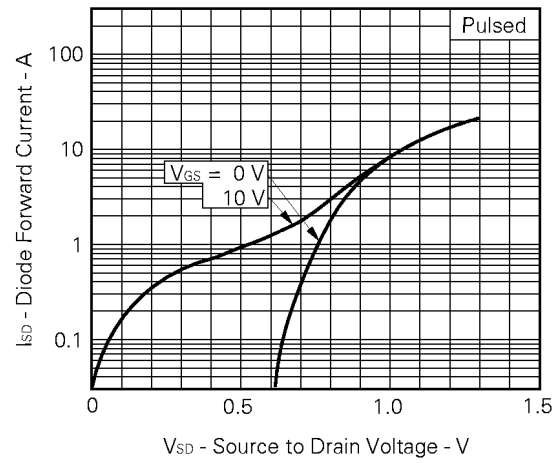
GATE TO SOURCE CUTOFF VOLTAGE vs. CHANNEL TEMPERATURE



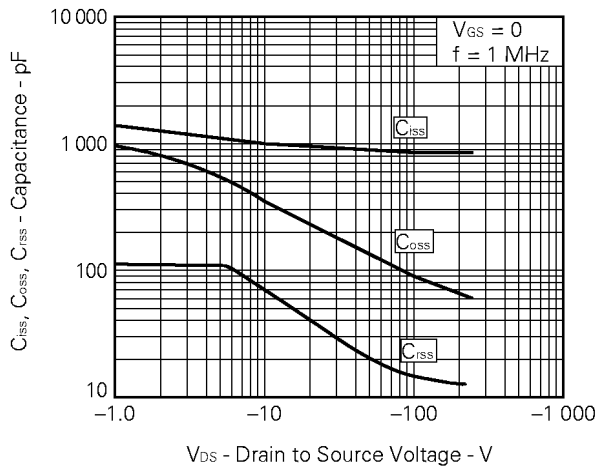
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



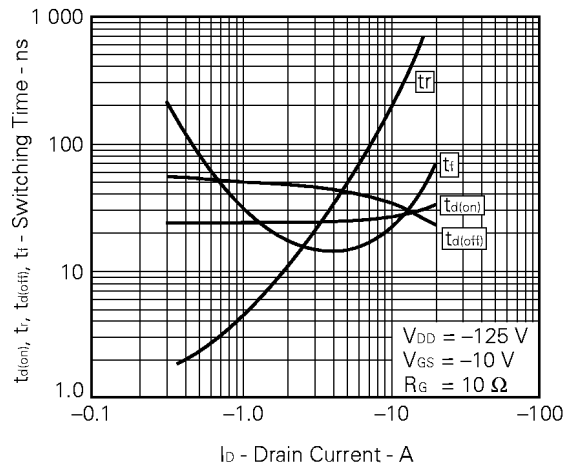
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



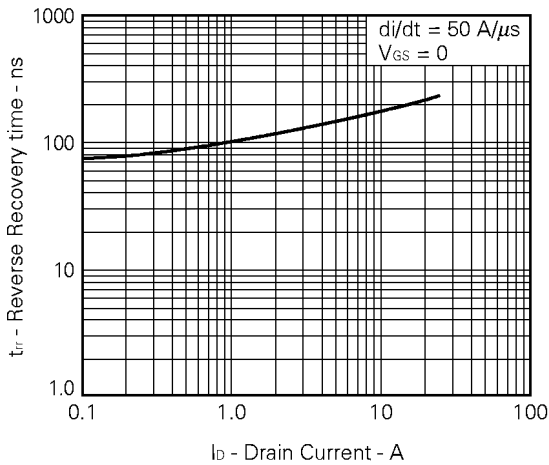
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



SWITCHING CHARACTERISTICS



REVERSE RECOVERY TIME vs. DRAIN CURRENT



DYNAMIC INPUT/OUTPUT CHARACTERISTICS

